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Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 14 (canceled)

15. (currently amended) A ~~manufacturing-method~~ of manufacture of a semiconductor integrated circuit device, comprising the steps of:

(a) forming a plurality of columnar laminates having, at ~~the~~ an upper portion and ~~a lower portions~~ portion thereof, a first semiconductor region and a second semiconductor region, respectively, while spacing the plurality of columnar laminates in a first direction and in a second direction wider than the first direction;

(b) forming conductive films over the side walls of the columnar laminates via a first insulating film with a distance, in the first direction, between the conductive films over the side walls of the plurality of columnar laminates as a first distance and with a distance in the second direction as a second distance which is greater than the first distance;

(c) forming a second insulating film to a thickness ~~enough~~ sufficient to fill a space of the first distance and but not ~~enough~~ sufficient to fill a space of the second distance; and

(d) forming a third insulating film over the second insulating film and filling the space of the second distance.

16. (currently amended) A ~~manufacturing-method~~ of manufacture of a semiconductor integrated circuit device, comprising the steps of:

(a) forming a plurality of columnar laminates having, at ~~the~~ an upper portion and ~~a lower portions~~ portion thereof, a first semiconductor region and a second semiconductor region, respectively, while spacing the plurality of columnar laminates in a first direction and in a second direction wider than the first direction;

(b) forming conductive films over the side walls of the columnar laminates via a first insulating film with a distance, in the first direction, between the conductive

films over the side walls of the plurality of columnar laminates as a first distance and with a distance in the second direction as a second distance which is greater than the first distance;

(c) depositing a second insulating film between the columnar laminates and thereover with a thickness at least equal to the first distance; and

(d) depositing over the second insulating film a third insulating film with a thickness corresponding to at least 70% of a vertical difference, after the step (c), between the top of the second insulating film over the second distance portion of the columnar laminates and the top of the second insulating film over the columnar laminates.

17. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the step (c) is carried out at a temperature of 700°C or less.

18. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the step (c) and the step (d) are carried out at a temperature of 700°C or less.

19. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device according to claim 15, further comprising, after the step (d), the steps of:

(e) depositing a fourth insulating film over the third insulating film; and

(f) etching the second, third and fourth insulating films until the conductive film existing over the side walls of the first semiconductor region of the columnar laminate is exposed.

20. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device according to claim 19, further comprising, after the step (g), a ~~steps~~ step of:

(h) forming a fifth insulating film over the second and third insulating films.

21. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device according to claim 15, further comprising, after the step (d), the steps of:

(e) etching the second and third insulating films until the conductive film existing over the side walls of the first semiconductor region of the columnar laminate is exposed; and

(f) etching the conductive film exposed by the step (e).

22. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 21, further comprising, after the step (f), a step of:

(g) forming a fourth insulating film over the second and third insulating films.

23. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the second insulating film has better coverage than the third insulating film.

24. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the second insulating film is a silicon oxide film and the step (c) is carried out by chemical vapor deposition using tetraethoxysilane as a raw material.

25. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the second insulating film is a silicon oxide film and the step (c) is carried out by chemical vapor deposition using tetraethoxysilane and ozone (O<sub>3</sub>) as raw materials.

26. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the third insulating film is a silicon oxide film and the step (d) is carried out in a plasma atmosphere having a plasma density of 10<sup>11</sup>/cm<sup>2</sup> or greater.

27. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the columnar laminate has a height of at least 3 times as much as the first distance.

28. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the first distance is 150 nm or less and the second distance is 500 nm or greater.

29. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the plane pattern of each of the columnar laminate and the conductive film over the side walls thereof is approximately elliptical and a first diameter in the first direction is smaller than a second diameter in the second direction.

30. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the columnar laminate in the step (a) is formed using a mask which is H-shaped in the first direction.

31. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device according to claim 15, further comprising, prior to the step (a), the steps of:

(h) forming two pairs of horizontal MISFETs having source and drain regions in common; and

(i) connecting the second semiconductor regions of the two vertical MISFETs adjacent to each other in the first direction to the source and drain regions which the two pairs of horizontal MISFETs have in common, respectively.

32. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device according to claim 15, further comprising, prior to the step (a), the steps of:

(j) forming two horizontal MISFETs; and

(k) connecting the second semiconductor regions of the two vertical MISFETs that are adjacent to each other in the first direction to one of the ends of the two horizontal MISFETs, respectively.

33. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device, comprising the steps of:

(a) forming a semiconductor film having, at the upper and lower portions thereof, first and second semiconductor regions, respectively;

(b) etching the semiconductor film through a mask which is H-shaped in a first direction, thereby forming an approximately elliptical columnar laminate having a longer diameter in a second direction perpendicular to the first direction; and

(c) forming a conductive film over the side walls of the approximately elliptical columnar laminate via an insulating film.

34. (currently amended) A ~~manufacturing~~ method of manufacture of a semiconductor integrated circuit device ~~comprising~~ including a plurality of vertical MISFETs, wherein the vertical MISFETs comprises:

(a1) a columnar laminate having, at the upper and lower portions thereof, first and second semiconductor regions, respectively, and

(a2) a conductive film formed over the side walls of the columnar laminate via a first insulating film;

wherein said plurality of vertical MISFETs having the columnar laminate and conductive film are

(b1) spaced by a first distance in a first direction, and

(b2) spaced by a second distance, which is greater than the first distance, in a second direction;

(c) the plane pattern of the columnar laminate and the conductive film over the side walls thereof being approximately elliptical, and a first diameter thereof in the first direction being smaller than a second diameter thereof in the second direction, the method comprising the steps of:

(d) forming a semiconductor film, having at the upper and lower portions thereof, first and second semiconductor regions, respectively; and

(e) etching the semiconductor film via a mask which is H-shaped in the first direction, thereby forming an approximately elliptical columnar laminate having a longer diameter in a second direction perpendicular to the first direction.

35. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 33, wherein the steps are for the formation of vertical MISFETs constituting a SRAM, and a single memory cell formation region of the SRAM is approximately rectangular with a long side in the second direction.

36. (currently amended) A method of manufacture of a semiconductor integrated circuit device according to claim 33, wherein the H-shaped mask is a transfer mask used in photolithography, an approximately elliptical columnar pattern for etching is formed using the H-shaped transfer mask, and the semiconductor film is processed into an approximately elliptical columnar laminate by using the etching pattern.

37. (currently amended) A method of manufacture of a semiconductor integrated circuit device according to claim 36, wherein the H-shaped mask has a structure in which the width of the mask in the first direction is narrower at the center of the mask in the second direction than at the both ends.

Claims 38 - 41 (canceled)

42. (currently amended) A ~~manufacturing~~-method of manufacture of a semiconductor integrated circuit device according to claim 15, wherein the conductive ~~film is~~ films are formed to encompass the columnar laminate laminates.